

## P-Channel Enhancement Mode Power MOSFET

### Description

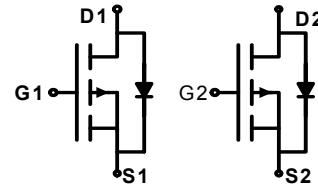
The HM4853A uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

### General Features

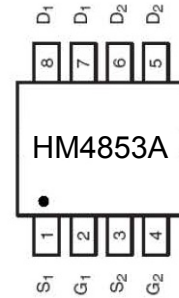
- $V_{DS} = -20V, I_D = -20A$   
 $R_{S(ON)} < 7m\Omega @ V_{GS} = -4.5V$   
 $R_{DS(ON)} < 9m\Omega @ V_{GS} = -2.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface Mount Package

### Application

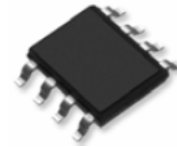
- Motor drive
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOP-8 top view

### Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM4853A	HM4853A	SOP-8	Ø330mm	12mm	2500 units

### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	-20	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	-60	A
Maximum Power Dissipation	$P_D$	3.1	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ\text{C}$

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	42	$^\circ\text{C/W}$
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### Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V

Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-20V, V_{GS}=0V$	-	-	-1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.6	-1.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-6A$	-	5.8	7.0	m $\Omega$
		$V_{GS}=-2.5V, I_D=-5A$		7.2	9.0	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-15V, I_D=-6A$	-	17	-	S
<b>Dynamic Characteristics</b> (Note4)						
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, V_{GS}=0V,$ $F=1.0MHz$	-	2100	-	PF
Output Capacitance	$C_{oss}$		-	498	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	300	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=10\Omega,$ $V_{GS}=-4.5V, R_{GEN}=6\Omega$	-	25	-	nS
Turn-on Rise Time	$t_r$		-	30	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	70	-	nS
Turn-Off Fall Time	$t_f$		-	50	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-10V, I_D=-6A, V_{GS}=-4.5V$	-	17	-	nC
Gate-Source Charge	$Q_{gs}$		-	4.1	-	nC
Gate-Drain Charge	$Q_{gd}$		-	4.3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-20A$	-	-	-1.2	V

## Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics



Figure 1 Switching Test Circuit



Figure 2 Switching Waveforms

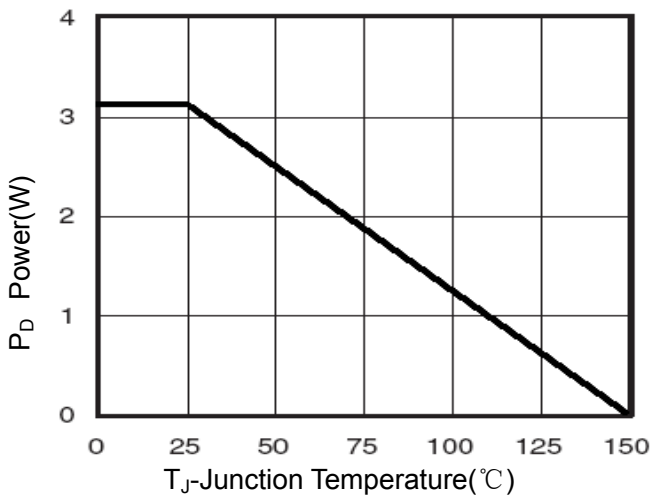


Figure 3 Power Dissipation

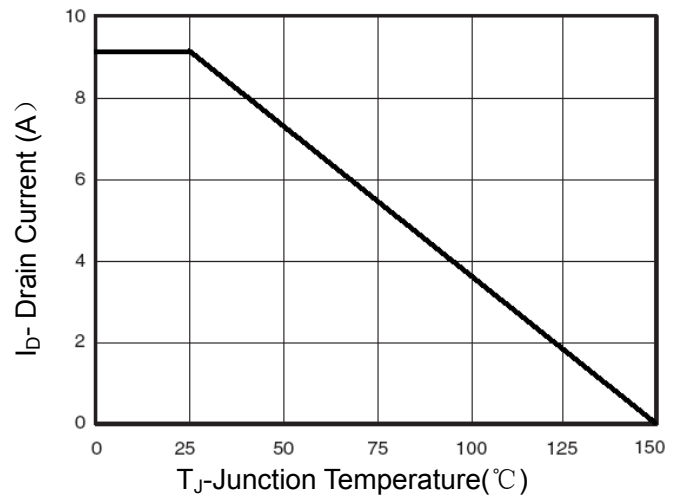


Figure 4 Drain Current

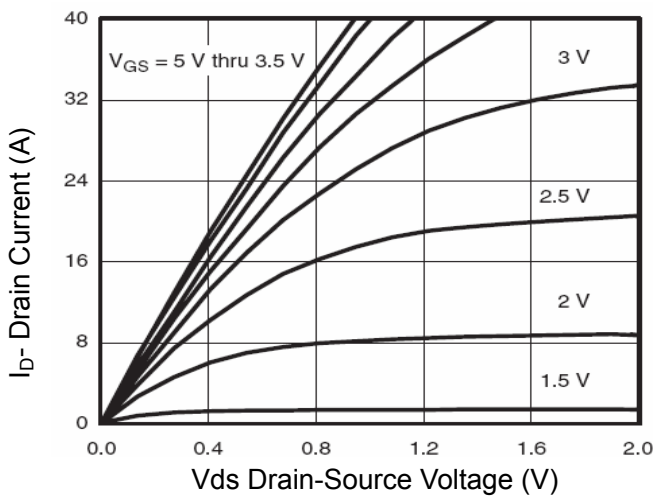


Figure 5 Output Characteristics

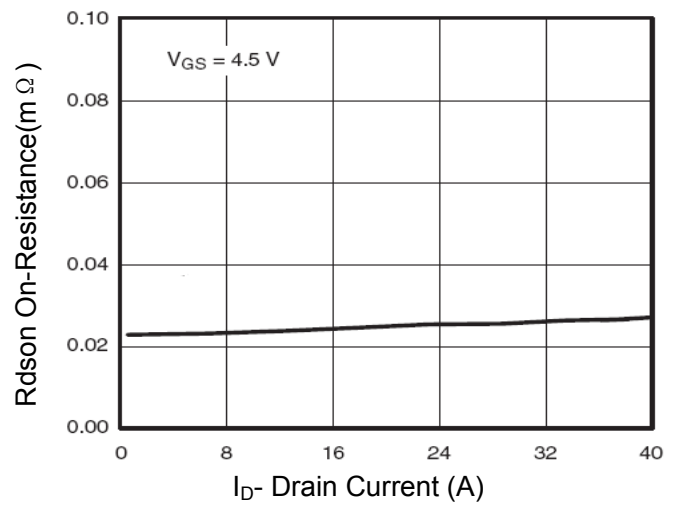


Figure 6 Drain-Source On-Resistance

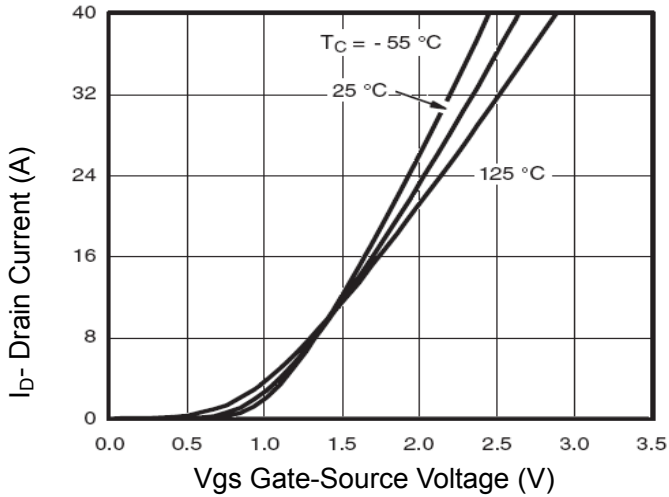


Figure 7 Transfer Characteristics

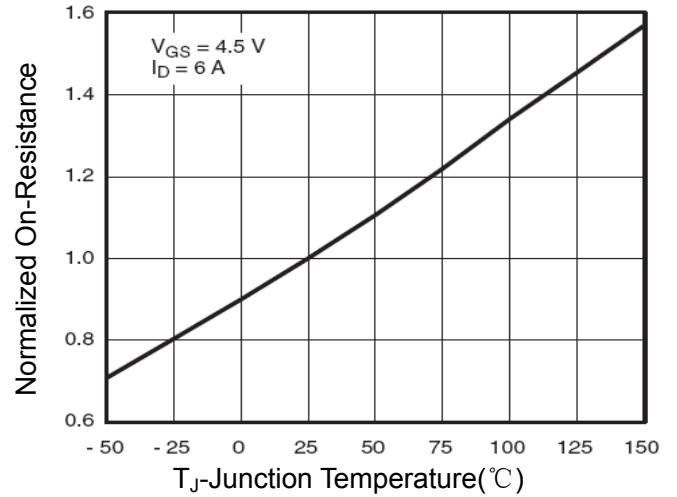


Figure 8 Drain-Source On-Resistance

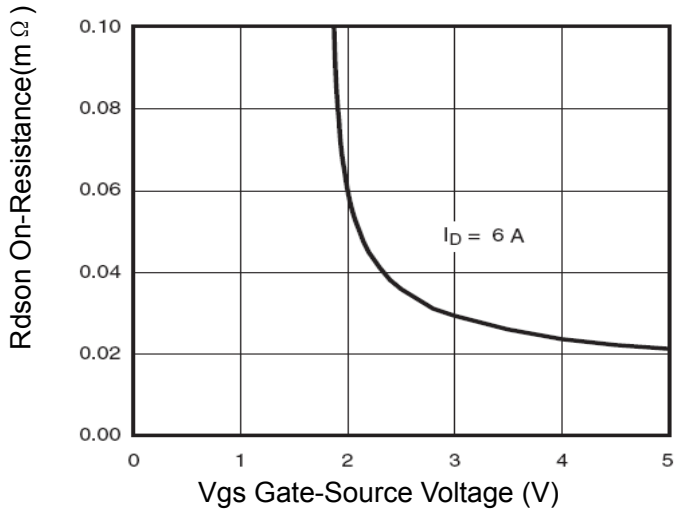


Figure 9 Rdson vs Vgs

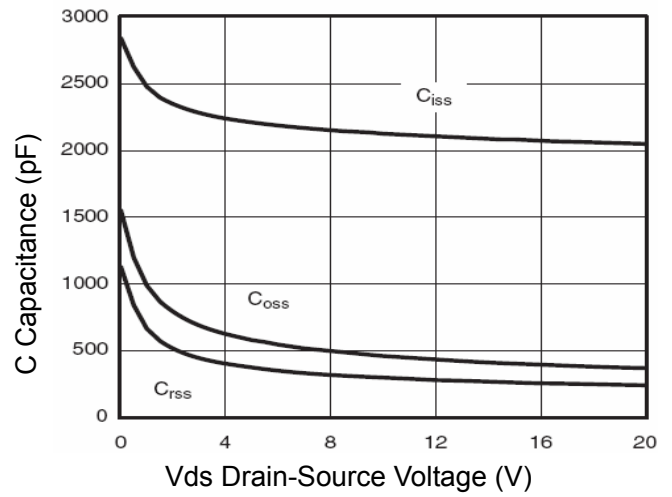


Figure 10 Capacitance vs Vds

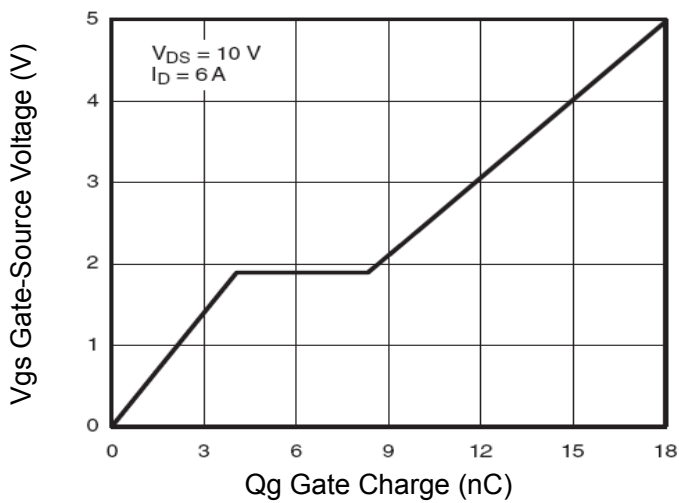


Figure 11 Gate Charge

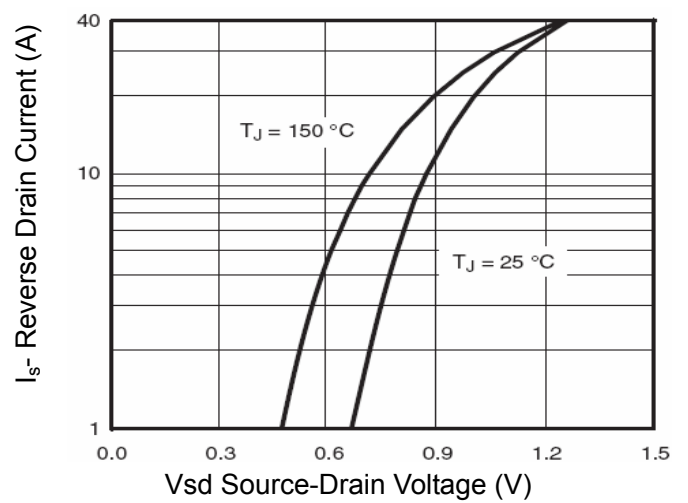


Figure 12 Source- Drain Diode Forward

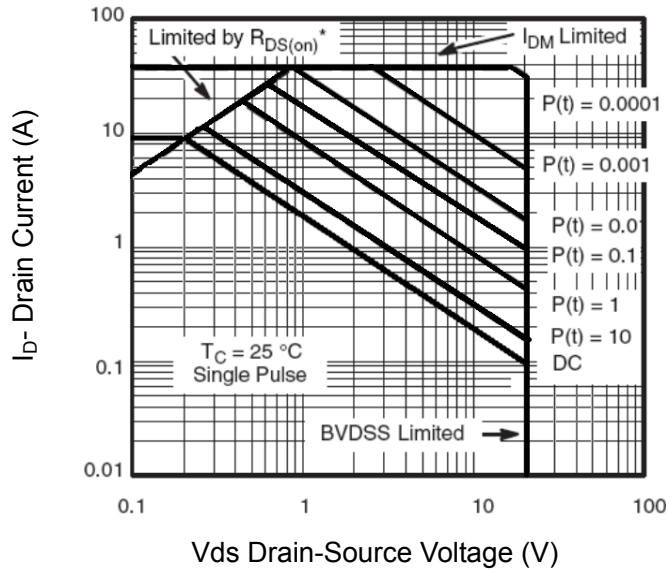


Figure 13 Safe Operation Area

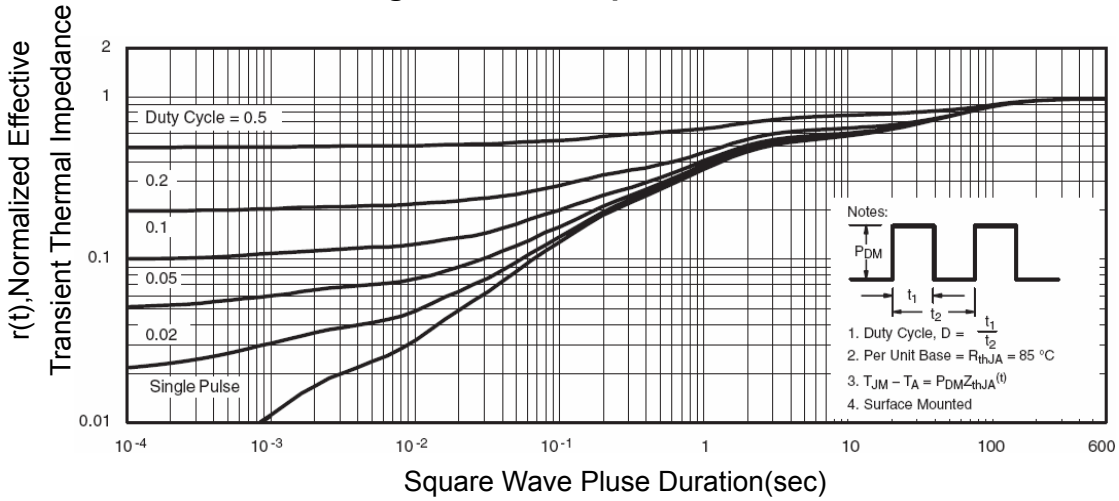
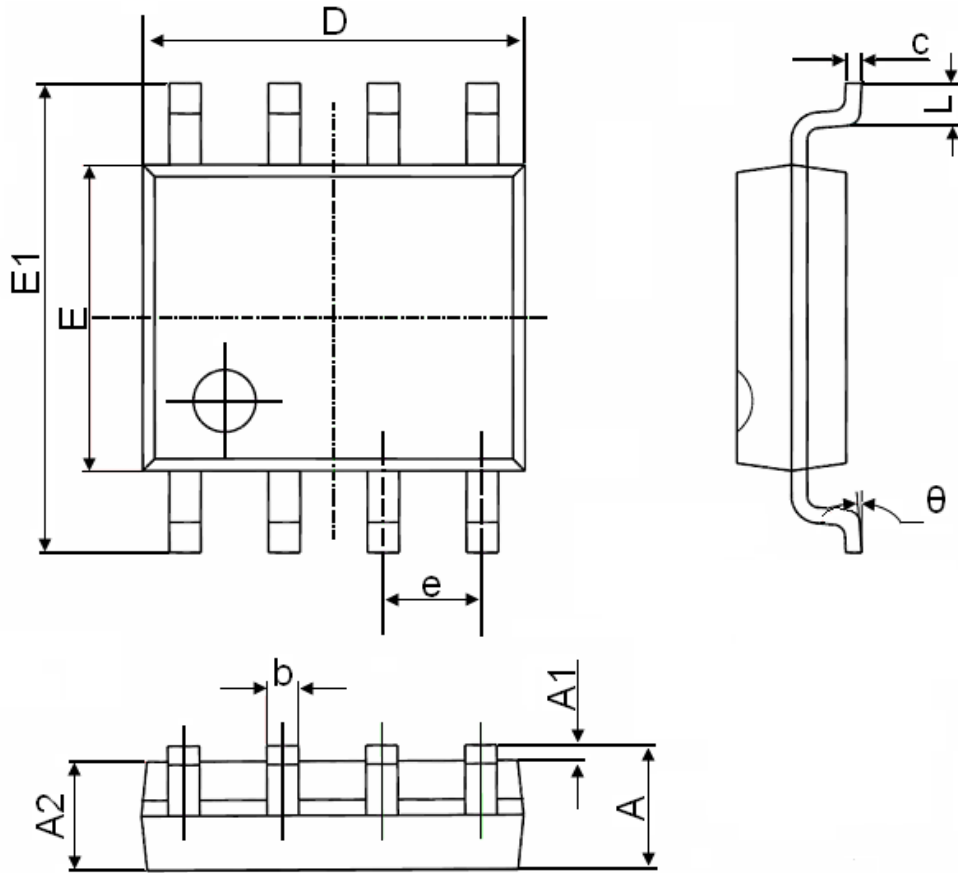


Figure 14 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
theta	0°	8°	0°	8°

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